TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# SSM5N05FU

#### **High Speed Switching Applications**

Unit: mm

• Small package

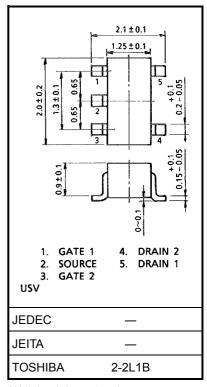
• Low on resistance :  $R_{on}$  = 0.8  $\Omega$  (max) (@VGS = 4 V) :  $R_{on}$  = 1.2  $\Omega$  (max) (@VGS = 2.5 V)

• Low gate threshold voltage

## Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristics		Symbol	Rating	Unit	
Drain-Source voltage		$V_{DS}$	20	V	
Gate-Source voltage		$V_{GSS}$	±12	V	
Drain current	DC	I <sub>D</sub>	400	mA	
	Pulse	$I_{DP}$	800		
Drain power dissipation (Ta = 25°C)		P <sub>D</sub> (Note1)	300	mW	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

Note1: Total rating, mounted on FR4 board (25.4 mm  $\times$  25.4 mm  $\times$  1.6 t, Cu Pad: 0.32 mm<sup>2</sup>  $\times$  5)



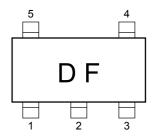
Weight: 6.2 mg (typ.)

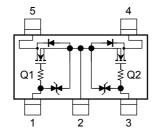
## **Handling Precaution**

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

#### Marking

#### **Equivalent Circuit (top view)**



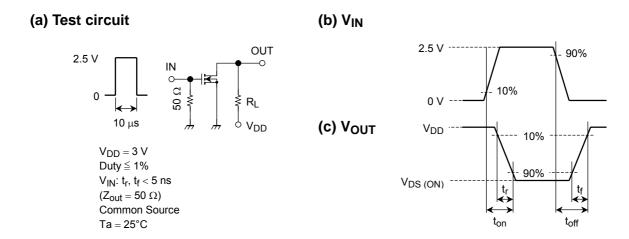


## Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0$	_	_	±1	μΑ
Drain-Source breakdown voltage		V (BR) DSS	$I_D = 1 \text{ mA}, V_{GS} = 0$	20	_	_	V
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0	_	_	1	μΑ
Gate threshold voltage		V <sub>th</sub>	$V_{DS} = 3 \text{ V}, I_D = 0.1 \text{ mA}$	0.6	_	1.1	V
Forward transfer admittance		Y <sub>fs</sub>	$V_{DS} = 3 \text{ V}, I_D = 200 \text{ mA}$ (Note2)	350	_	_	mS
Drain-Source ON resistance		R <sub>DS (ON)</sub>	$I_D = 200 \text{ mA}, V_{GS} = 4 \text{ V}$ (Note2)	_	0.6	0.8	Ω
			$I_D = 200 \text{ mA}, V_{GS} = 2.5 \text{ V}$ (Note2)	_	0.85	1.2	
Input capacitance		C <sub>iss</sub>		_	22	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	9	_	pF
Output capacitance		C <sub>oss</sub>		_	21	_	pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = 3 \text{ V}, I_D = 100 \text{ mA},$	_	60	_	ns
	Turn-off time	t <sub>off</sub>	V <sub>GS</sub> = 0~2.5 V	_	70	_	

Note2: Pulse test

### **Switching Time Test Circuit**

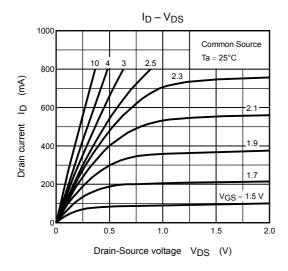


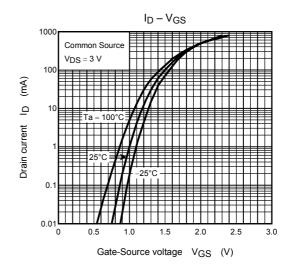
#### **Precaution**

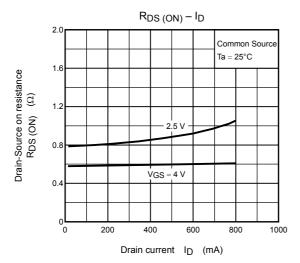
 $V_{th} \ can \ be \ expressed \ as \ voltage \ between \ gate \ and \ source \ when \ low \ operating \ current \ value \ is \ I_D = 100 \ \mu A \ for \ this \ product.$  For normal switching operation,  $V_{GS}$  (on) requires higher voltage than  $V_{th}$  and  $V_{GS}$  (off) requires lower voltage than  $V_{th}$ . (Relationship can be established as follows:  $V_{GS}$  (off)  $< V_{th} < V_{GS}$  (on) )

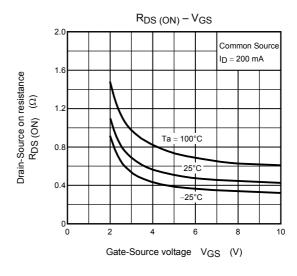
Please take this into consideration for using the device.  $V_{\rm GS}$  recommended voltage of 2.5 V or higher to turn on this product.

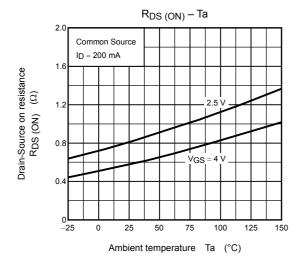
(Q1, Q2 common)

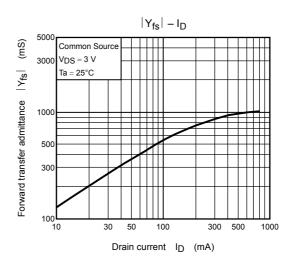






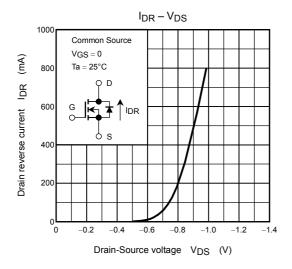


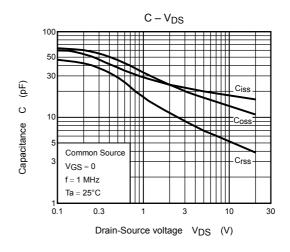


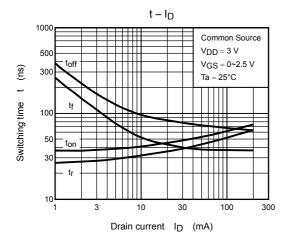


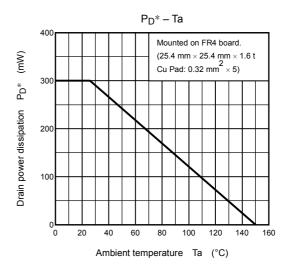
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(Q1, Q2 common)









\*: Total rating

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